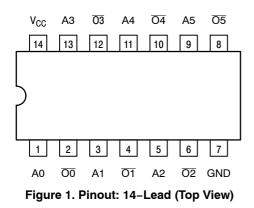
Low-Voltage CMOS Hex Inverter with Open Drain Outputs

With 5 V – Tolerant Inputs

The MC74LCX06 is a high performance hex inverter operating from a 2.3 V to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers. These LCX devices have open drain outputs which provide the ability to set output levels, or do active–HIGH AND or active–LOW OR functions. A V_I specification of 5.5 V allows MC74LCX06 inputs to be safely driven from 5.0 V devices.

Features

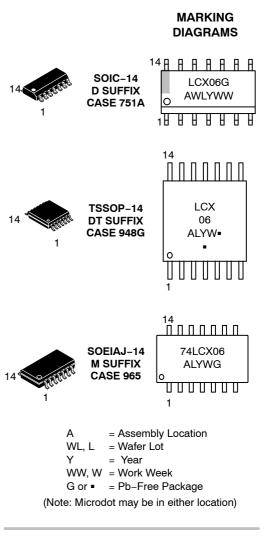
- Designed for 2.3 V to 3.6 V V_{CC} Operation
- 5.0 V Tolerant Inputs/Outputs
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Output Sink Capability
- Near Zero Static Supply Current (10 µA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- Wired-OR, Wired-AND
- Output Level Can Be Set Externally Without Affecting Speed of Device
- Functionally Compatible with LCX05
- ESD Performance: Human Body Model >1500 V; Machine Model >200 V
- These Devices are Pb-Free and are RoHS Compliant





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ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

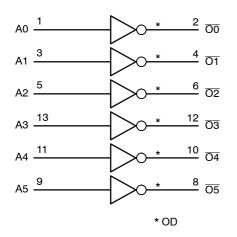


Figure 2. Logic Diagram

Table 1. PIN NAMES

Pins	Function
An	Data Inputs
On	Outputs

Table 2. TRUTH TABLE

An	Ōn
L	Z
H	L

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_{l} \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le +7.0$	Output in HIGH or LOW State (Note 1)	V
l _{IK}	DC Input Diode Current	-50	V _I < GND	mA
Ι _{ΟΚ}	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
lo	DC Output/Sink Current	+50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected. 1. I_O absolute maximum rating must be observed.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LCX06DG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74LCX06DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74LCX06DTG	TSSOP-14*	96 Units / Rail
MC74LCX06DTR2G	TSSOP-14*	2500 / Tape & Reel
MC74LCX06MG	SOEIAJ-14	50 Units / Rail
MC74LCX06MELG	SOEIAJ-14	2000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Тур	Max	Unit
V _{CC}	Supply Voltage	Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
Vo	Output Voltage	(HIGH or LOW State)	0		V _{CC}	V
I _{OL}	LOW Level Output Current Sink	$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			+24 +12 +8	mA
T _A	Operating Free-Air Temperature		-40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V	IN from 0.8 V to 2.0 V, V _{CC} = 3.0 V	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS (T_A = $-40^{\circ}C$ to $+85^{\circ}C$)

Symbol	Characteristic	Condition	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage (Note 2)	$2.3~\text{V} \leq \text{V}_{\text{CC}} \leq 2.7~\text{V}$	1.7		V
		$2.7~V \leq V_{CC} \leq 3.6~V$	2.0		
V _{IL}	LOW Level Input Voltage (Note 2)	$2.3~\text{V} \leq \text{V}_{\text{CC}} \leq 2.7~\text{V}$		0.7	V
		$2.7 \text{ V} \leq \text{V}_{\text{CC}} \leq 3.6 \text{ V}$		0.8	
V _{OL}	LOW Level Output Voltage	2.3 V \leq V_{CC} \leq 3.6 V; I_{OL} = 100 μA		0.2	V
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.3	
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4	1
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4	1
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	1
I _I	Input Leakage Current	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±5.0	μA
I _{OFF}	Power-Off Leakage Current	V_{CC} = 0 V; V _I or V _O = 5.5 V		10	μA
I _{CC}	Quiescent Supply Current	2.3 V \leq V_{CC} \leq 3.6 V; V_I = GND or V_{CC}		10	μA
		$2.3~V \leq V_{CC} \leq 3.6~V;~3.6 \leq V_I \leq 5.5~V$	1	±10	μΑ
ΔI_{CC}	Increase in I _{CC} per Input	$2.3~V \le V_{CC} \le 3.6~V$ One Input at V_{IH} = V_{CC} – 0.6 V		500	μΑ

2. These values of V_I are used to test DC electrical characteristics only.

AC ELECTRICAL CHARACTERISTICS (T_A = -40° C to $+85^{\circ}$ C)

		V_{CC} = 3.3 V \pm 0.3 V C_L = 50 pF		V _{CC} = 2.7 V C _L = 50 pF		$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V} \\ C_L = 30 \text{ pF}$		
Symbol	Parameter	Min	Мах	Min	Max	Min	Мах	Unit
t _{PLZ} t _{PZL}	Propagation Delay Input to Output	0.8 0.8	3.7 3.7	1.0 1.0	4.1 4.1	0.8 0.8	3.5 3.5	ns ns

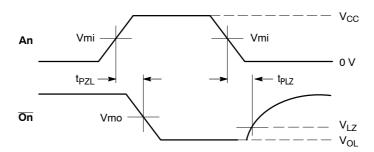
DYNAMIC SWITCHING CHARACTERISTICS (T_A = $+25^{\circ}$ C)

Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 3)			0.9 0.7		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 3)	$ \begin{array}{l} V_{CC} = 3.3 \text{ V}, \ C_L = 50 \text{ pF}, \ V_{IH} = 3.3 \text{ V}, \ V_{IL} = 0 \text{ V} \\ V_{CC} = 2.5 \text{ V}, \ C_L = 30 \text{ pF}, \ V_{IH} = 2.5 \text{ V}, \ V_{IL} = 0 \text{ V} \end{array} $		-0.8 -0.6		V

 Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	7	pF
C _{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	25	pF



PROPAGATION DELAYS t_R = t_F = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns

Table 3. AC WAVEFORMS

	V _{CC}					
Symbol	$3.3 V \pm 0.3 V$	2.7 V	$2.5 V \pm 0.2 V$			
V _{mi}	1.5 V	1.5 V	V _{CC} / 2			
V _{mo}	1.5 V	1.5 V	V _{CC} / 2			
V_{LZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V			

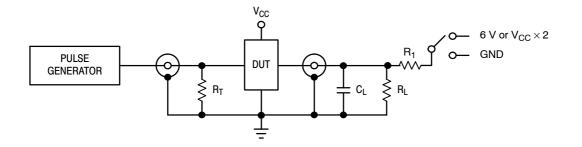


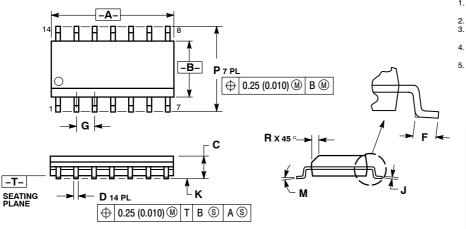
Table 4. TEST CIRCUIT

TEST	SWITCH
t _{PZL} , t _{PLZ}	6 V
Open Collector/Drain $t_{\mbox{PLH}}$ and $t_{\mbox{PHL}}$	6 V
t _{PZH} , t _{PHZ}	GND

 $\begin{array}{l} C_L = 50 \ \text{pF} \ \text{at} \ V_{CC} = \ 3.3 \ \pm \ 0.3 \ \text{V} \ \text{or equivalent} \ (\text{includes jig and} \\ \text{probe capacitance}) \\ C_L = \ 30 \ \text{pF} \ \text{at} \ V_{CC} = \ 2.5 \ \pm \ 0.2 \ \text{V} \ \text{or equivalent} \ (\text{includes jig and} \\ \text{probe capacitance}) \\ R_L = \ R_1 = 500 \ \Omega \ \text{or equivalent} \\ R_T = \ Z_{OUT} \ \text{of pulse generator} \ (\text{typically 50 } \Omega) \end{array}$

PACKAGE DIMENSIONS

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE J**

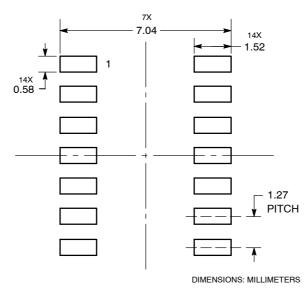


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLEHANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 DIMENSION DOCE NOT INCLUDE
- PER SIDE. 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES		
DIM	MIN MAX		MIN	MAX		
Α	8.55	8.75	0.337	0.344		
В	3.80	4.00	0.150	0.157		
С	1.35	1.75	0.054	0.068		
D	0.35	0.49	0.014	0.019		
F	0.40	1.25	0.016	0.049		
G	1.27	BSC	0.050 BSC			
J	0.19	0.25	0.008	0.009		
κ	0.10	0.25	0.004	0.009		
М	0 °	7 °	0 °	7 °		
Ρ	5.80	6.20	0.228	0.244		
R	0.25	0.50	0.010	0.019		

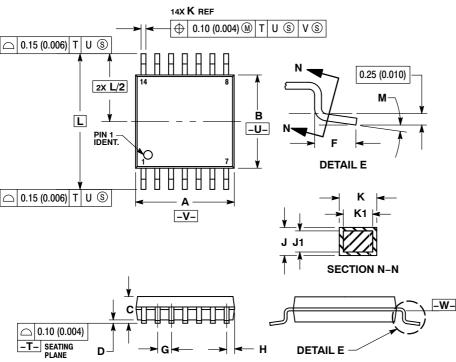
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE B**

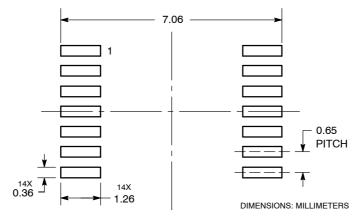


NOTES:

- OTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. S. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
к	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Г	6.40 BSC		0.252 BSC	
Μ	0 °	8 °	0 °	8 °

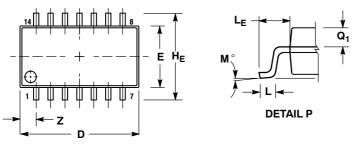
SOLDERING FOOTPRINT*

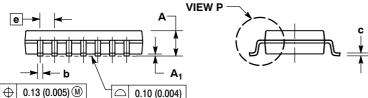


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOEIAJ-14 M SUFFIX CASE 965-01 ISSUE B





NOTES:

 I. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.

CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE
 MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE. MOLD FLASH
 OR PROTRUSIONS SHALL NOT EXCEED 0.15

(0.006) PER SIDE. 4. TERMINAL NUMBERS ARE SHOWN FOR

REFERENCE ONLY. 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
М	0 °	10 °	0 °	10 °
Q ₁	0.70	0.90	0.028	0.035
Ζ		1.42		0.056

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